

Spezifikationen	
Artikelnummer	QS5U36TR
Hersteller	LAPIS Semiconductor
Beschreibung	MOSFET N-CH 20V 2.5A TSMT5
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	108242 pcs Stock
VGS (th) (Max) @ Id	1.3V @ 1mA
Vgs (Max)	±10V
Technologie	MOSFET (Metal Oxide)
Supplier Device-Gehäuse	TSMT5
Serie	-
Rds On (Max) @ Id, Vgs	81 mOhm @ 2.5A, 4.5V
Verlustleistung (max)	1.25W (Ta)
Verpackung	Tape & Reel (TR)
Verpackung / Gehäuse	SOT-23-5 Thin, TSOT-23-5
Betriebstemperatur	150°C (TJ)
Befestigungsart	Surface Mount
Eingabekapazität (Ciss) (Max) @ Vds	280pF @ 10V
Gate Charge (Qg) (Max) @ Vgs	3.5nC @ 4.5V
Typ FET	N-Channel
FET-Merkmal	Schottky Diode (Isolated)
Antriebsspannung (Max Rds On, Min Rds On)	1.5V, 4.5V
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	2.5A (Ta)

sein:

The central logo features the letters "YIC" in a stylized, blue, outlined font. Below it, the text "Not Actual Photo" is written in a small, black, sans-serif font, followed by "YIC Industrial Co., Limited." in a slightly larger, bold, black, sans-serif font. The components are arranged in a circular pattern around the logo, with some components appearing to be floating or falling towards the bottom.

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QS5U34 ROHM

 QS5U33TR Rohm Semiconductor MOSFET P-CH 30V 2A TSMT5	 QS5U34TR MOSFETIGBTIC ROHM ROHM SOT23-5	 QS5W1TR Rohm Semiconductor TRANS 2NPN 30V 3A TSMT5
 QS5V993-2QC IDT IDT TSOP-28	 QS5V991-5JRI QS QS PLCC32	 QS5V9910-2SOC QS QS SOP24

Mehr

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HINZUFÜGEN: Einheit A5-B5 Nr. 509, 5 / F Sing Win-Fabrikgebäude, 15-17 Shing Yip Street, Kwun Tong, Kowloon, Hongkong.

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